

IN THE CLAIMS

Please amend claims 25 and 42 as follows.

Claims 26-41 and 43-60 are re-presented.

PENDING CLAIMS

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25. (Amended Once) A microelectronic structure comprising:
a gate electrode; and
a source/drain terminal aligned with the gate electrode, the source/drain terminal comprising an implanted region, a first silicide layer in the implanted region, and a second silicide layer in the implanted region.
26. The microelectronic structure of claim 25, wherein the second silicide layer is thicker than the first silicide layer.
27. The microelectronic structure of claim 25, wherein the second silicide layer is spaced from the gate electrode.
28. The microelectronic structure of claim 25, comprising another source/drain terminal aligned with the gate electrode, the other source/drain terminal comprising an implanted region and two silicide layers.

29. The microelectronic structure of claim 25, wherein the first and second silicide layers comprise different metals.
30. The microelectronic structure of claim 25, wherein the first and second silicide layers comprise the same metal.
31. The microelectronic structure of claim 25, wherein the first silicide layer comprises CoSi_2 .
32. The microelectronic structure of claim 25, wherein the first silicide layer comprises TiSi_2 .
33. The microelectronic structure of claim 25, wherein the second silicide layer comprises nickel silicide.
34. The microelectronic structure of claim 25, wherein the second silicide layer comprises CoSi_2 .
35. The microelectronic structure of claim 25, wherein the second silicide layer comprises TiSi_2 .
36. The microelectronic structure of claim 25, comprising a silicidation barrier adjacent the gate electrode.

37. The microelectronic structure of claim 36, wherein the silicidation barrier comprises silicon nitride.

38. The microelectronic structure of claim 25, comprising a silicide layer adjacent the gate electrode.

39. The microelectronic structure of claim 38, wherein the silicide layer adjacent the gate electrode comprises nickel silicide.

40. The microelectronic structure of claim 38, wherein the silicide layer adjacent the gate electrode comprises CoSi_2 .

41. The microelectronic structure of claim 38, wherein the silicide layer adjacent the gate electrode comprises TiSi_2 .

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42. (Amended Once) A microelectronic structure comprising:
a gate electrode; and
a source/drain terminal aligned with the gate electrode, the source/drain terminal comprising a first implanted region, a first silicide layer in the first implanted region, a second implanted region, and a second silicide layer in the second implanted region.

43. The microelectronic structure of claim 42, wherein the first silicide layer is contained within the first implanted region.

44. The microelectronic structure of claim 42, wherein the second silicide layer is thicker than the first implanted region.

45. The microelectronic structure of claim 42, wherein the second implanted region is thicker than the first implanted region.

46. The microelectronic structure of claim 42, wherein the second implanted region and the second silicide layer are spaced from the gate electrode.

47. The microelectronic structure of claim 42, comprising another source/drain terminal aligned with the gate electrode, the other source/drain terminal comprising two implanted regions and two silicide layers.

48. The microelectronic structure of claim 42, wherein the first and second silicide layers comprise different metals.

49. The microelectronic structure of claim 42, wherein the first and second silicide layers comprise the same metal.

50. The microelectronic structure of claim 42, wherein the first silicide layer comprises CoSi_2 .
51. The microelectronic structure of claim 42, wherein the first silicide layer comprises TiSi_2 .
52. The microelectronic structure of claim 42, wherein the second silicide layer comprises nickel silicide.
53. The microelectronic structure of claim 42, wherein the second silicide layer comprises CoSi_2 .
54. The microelectronic structure of claim 42, wherein the second silicide layer comprises TiSi_2 .
55. The microelectronic structure of claim 42, comprising a silicidation barrier adjacent the gate electrode.
56. The microelectronic structure of claim 55, wherein the silicidation barrier comprises silicon nitride.
57. The microelectronic structure of claim 42, comprising a silicide layer adjacent the gate electrode.

58. The microelectronic structure of claim 57, wherein the silicide layer adjacent the gate electrode comprises nickel silicide.

59. The microelectronic structure of claim 57, wherein the silicide layer adjacent the gate electrode comprises CoSi_2 .

60. The microelectronic structure of claim 57, wherein the silicide layer adjacent the gate electrode comprises TiSi_2 .